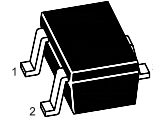
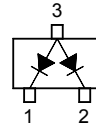


MMBD202CAW

Silicon Epitaxial Planar Switching Diode

Application

- Ultra high speed switching



SOT-323 Plastic Package

Marking Code: YX

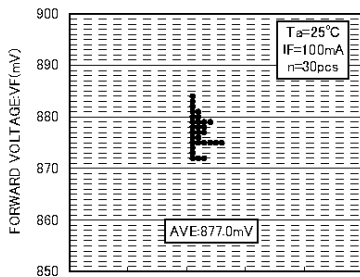
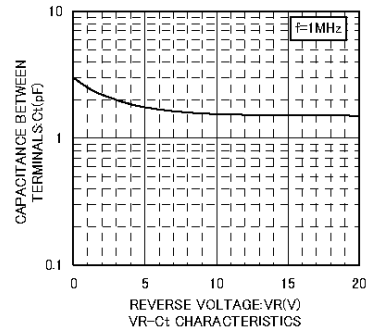
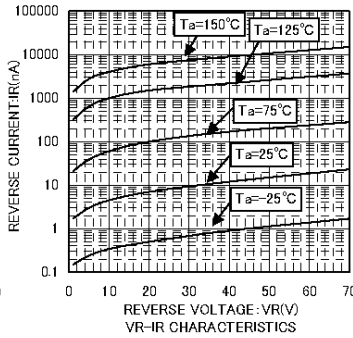
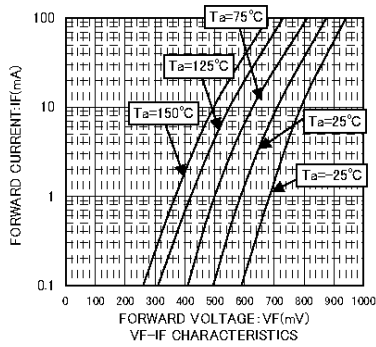
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|-------------|---------------|------------------|
| Maximum Peak Reverse Voltage | V_{RM} | 80 | V |
| Reverse Voltage | V_R | 80 | V |
| Average Forward Current (Single) | $I_{F(AV)}$ | 100 | mA |
| Maximum Peak Forward Current (Single) | I_{FM} | 300 | mA |
| Non-repetitive Peak Forward Surge Current ($t = 1\text{ }\mu\text{s}$) | I_{FSM} | 4 | A |
| Power Dissipation | P_{tot} | 200 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

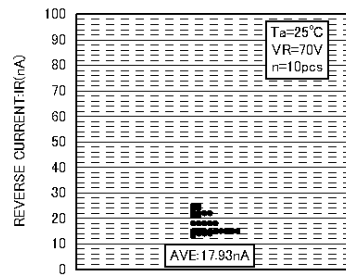
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|---|----------|------|---------------|
| Forward Voltage at $I_F = 100\text{ mA}$ | V_F | 1.2 | V |
| Reverse Current at $V_R = 70\text{ V}$ | I_R | 0.1 | μA |
| Capacitance Between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$ | C_T | 3.5 | pF |
| Reverse Recovery Time at $V_R = 6\text{ V}$, $I_F = 5\text{ mA}$, $R_L = 50\text{ }\Omega$ | t_{rr} | 4 | ns |

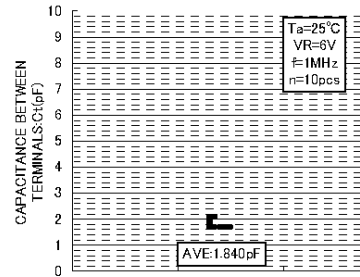
MMBD202CAW



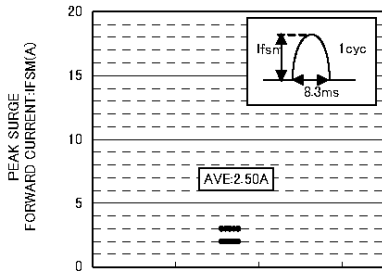
VF DISPERSION MAP



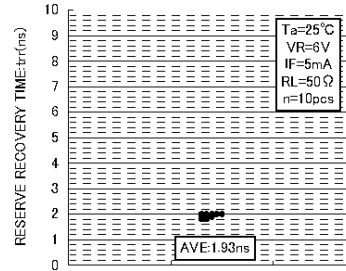
IR DISPERSION MAP



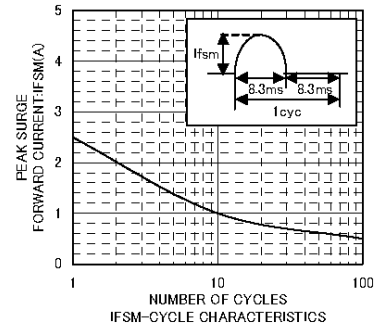
Ct DISPERSION MAP



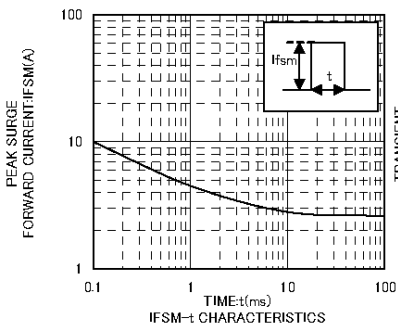
IFSM DISERSION MAP



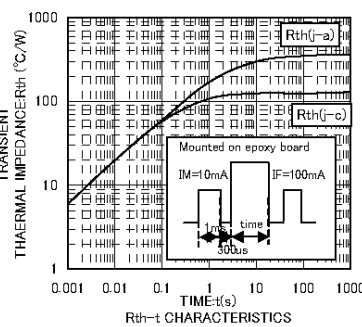
trr DISPERSION MAP



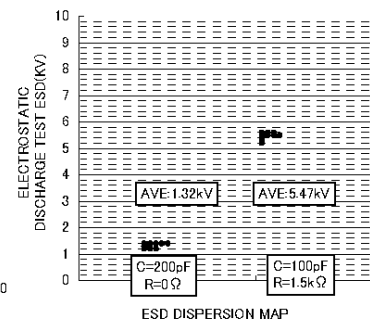
IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



ESD DISPERSION MAP